

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Priority Application Serial No. 10/264,914
Priority Filing Date October 3, 2002
Inventor Arup Bhattacharyya
Assignee Micron Technology, Inc.
Priority Group Art Unit 2823
Priority Examiner Brook Kebede
Attorney's Docket No. MI22-2473
Title: High Performance Three-Dimensional TFT-Based CMOS Inverters, and Computer
Systems Utilizing Such Novel CMOS Inverters

INFORMATION DISCLOSURE STATEMENT

References - - See attached Form PTO-1449

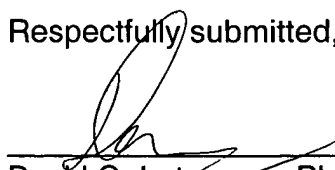
In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the references listed on the attached Form PTO-1449. No admission is made regarding whether all the submitted references are prior art.

The listed references were cited by, or submitted to, the Office in the parent, co-pending application of the above-identified application. The above-identified application is a continuation of co-pending application Serial No. 10/264,914, filed October 3, 2002, upon which the above-identified application relies for a priority date under 35 U.S.C. §120.

Citation of these references is respectfully requested.

Date: 11/14/04

Respectfully submitted,



David G. Latwesen, Ph.D.
Reg. No. 38,533

EV318280352

MyeSrsForm PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-2473	SERIAL NO. Filed Herewith
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Arup Bhattacharyya	
				FILING DATE Filed Herewith	GROUP Unassigned
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)					
	AA		Ono, K. et al., "Analysis of Current-Voltage Characteristics in Polysilicon TFTs for LCDs", IEDM Tech. Digest, 1988, pp. 256-259.		
	AB		Yamauchi, N. et al., "Drastically Improved Performance in Poly-Si TFTs with Channel Dimensions Comparable to Grain Size", IEDM Tech. Digest, 1989, pp. 353-356.		
	AC		King, T. et al, "A Low-Temperature ($\leq 550^\circ\text{C}$) Silicon-Germanium MOS Thin-Film Transistor Technology for Large-Area Electronics", IEDM Tech. Digest, 1991, pp. 567-570.		
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EXAMINER			DATE CONSIDERED		
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	AM		Feder, B.J., "I.B.M. Finds Way to Speed Up Chips", The New York Times, June 8, 2001, reprinted from http://www.nytimes.com/2001/06/08/technology/08BLUE.html , 2 pgs.		
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